PNP High Power Silicon Transistor



Rev. V3

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/379
- TO-3 (TO-204AA) Package
- Designed for High Power, Medium Speed Switching and Amplifier Applications



Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I _C = -10 mA dc; 2N3791 I _C = -10 mA dc; 2N3792	V _{(BR)CEO}	V dc	-60 -80	_
Collector - Emitter Cutoff Current	V_{CE} = -60 V dc; V_{BE} = -1.5 V dc, 2N3791 V_{CE} = -80 V dc; V_{BE} = -1.5 V dc, 2N3792	I _{CEX}	µA dc	_	-20 -20
Collector - Base Cutoff Current	V _{CE} = -60 V dc, 2N3791 V _{CE} = -80 V dc, 2N3792	I _{CBO}	µA dc	—	-20 -20
Emitter - Base Cutoff Current	V _{EB} = -7 V dc	I _{EBO}	mA dc	_	-5.0
Collector-Emitter Cutoff Current	V _{CE} = -50 V dc, 2N3791 V _{CE} = -70 V dc, 2N3792	I _{CES1}	µA dc		-20 -20
		T	1 1		
Forward Current Transfer Ratio	$V_{CE} = -2.0 V dc; I_C = -1.0 A dc$ $V_{CE} = -2.0 V dc; I_C = -3.0 A dc$ $V_{CE} = -2.0 V dc; I_C = -5 A dc$ $V_{CE} = -4.0 V dc; I_C = -10 A dc$	h _{FE}	-	50 30 10 5	150 120
Collector - Emitter Saturation Voltage	$I_{C} = -5 \text{ A dc}; I_{B} = -0.5 \text{ A dc}$ $I_{C} = -10 \text{ A dc}; I_{B} = -2.0 \text{ A dc}$	$\begin{array}{c} V_{CE(sat)1} \\ V_{CE(sat)2} \end{array}$	Vdc	—	-1.0 -2.5
Base - Emitter Saturation Voltage	$I_{C} = -5 \text{ A dc}; I_{B} = -0.5 \text{ Vdc}$ $I_{C} = -10 \text{ A dc}; I_{B} = -2.0 \text{ Vdc}$	$\begin{array}{c} V_{BE(sat)1} \\ V_{BE(sat)2} \end{array}$	Vdc	—	-1.5 -3.0
Collector-Emitter Cutoff Current	$T_A = +150^{\circ}C$ $V_{CE} = -50 V dc, 2N3791$ $V_{CE} = -70 V dc, 2N3792$	I _{CES2}	mA dc		-3.4 -3.4
Forward Current Transfer Ratio	$T_A = -55^{\circ}C$ V _{CE} = -2.0 V dc; I _C = -3.0 A dc	h _{FE5}		12	
Oynamic Characteristics					
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	V_{CE} = -10 V dc; I _C = -0.5 A dc; f = 1 MHz	h _{fe}		4.0	20
Small-Signal Short-Circuit Forward Current Transfer Ratio	V_{CE} = -10 V dc; I _C = -0.5 A dc; f = 1 kHz	h _{fe}		30	300
Open Circuit Output Capacitance	V _{CB} = -10 V dc; I _E = 0; f = 1MHz	C _{obo}	pF	_	500

¹

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Parameter Switching Characteristics	Test Conditions	Symbol	Units	Min.	Max.
Delay Time Rise Time Storage Time Fall Time	See figure 4 of MIL-PRF-19500/379	t _d t _r t _s t _f	μs	_	0.2 1.3 1.4 1.0

Absolute Maximum Ratings ($T_c = +25^{\circ}C$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N3791 2N3792	V _{CEO}	-60 V dc -80 V dc
Collector - Base Voltage 2N3791 2N3792	V _{CBO}	-60 V dc -80 V dc
Emitter - Base Voltage	V_{EBO}	-7 V dc
Base Current	Ι _Β	-4 V dc
Collector Current	Ι _C	-10 A dc
Total Power Dissipation @ $T_A = +25^{\circ}C^{(1)}$ @ $T_C = +100^{\circ}C^{(2)}$	P _T	5.0 W 85.7 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

(1) Derate linearly 28.57 mW/°C above T_A = +25°C.

(2) See figure 2 of Mil-PRF-19500/379 for temperature-power derating curves.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	R _{θJC}	1.1°C/W

Safe Operating Area	
DC Tests:	T _C = +25°C, I Cycle, t <u>></u> 1.0 s
Test 1:	V_{CE} = -15 V dc; I _C = -10 A dc
Test 2:	V_{CE} = -40 V dc; I _C = -3.75 A dc
Test 3:	V _{CE} = -55 V dc; I _C = -0.9 A dc, 2N3791 V _{CE} = -65 V dc; I _C = -0.9 A dc, 2N3792

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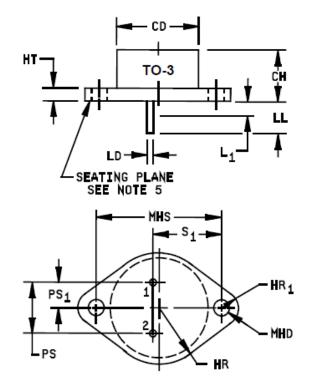
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Outline Drawing (TO-3)

	Dimensions				
Ltr Inc		hes	Millimeters		Notes
	Min	Max	Min	Max	
CD		.875		22.22	
CH	.270	.350	6.86	8.89	
HR	.495	.525	12.57	13.34	
HR ₁	.131	.188	3.33	4.78	
HT	.060	.135	1.52	3.43	
LD	.038	.043	0.97	1.09	7
LL	.312	.500	7.92	12.70	
L ₁		.050		1.27	7
MHD	.151	.165	3.84	4.19	
MHS	1.177	1.197	29.90	30.40	
PS	.420	.440	10.67	11.18	4,5
PS ₁	.205	.225	5.21	5.72	4,5
S ₁	.655	.675	16.64	17.15	4



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Terminal 2, base; terminal 1, emitter; case, collector.
- These dimensions should be measured at points .050 inch (1.27 mm) to .055 inch (1.40 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
- The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
- 6. Collector shall be electrically connected to the case.
- 7. LD applies between L1 and LL. Lead diameter shall not exceed twice LD within L1.
- 8. In accordance with ASME Y14.5M, diameters are equivalent to \$\$\phix\$ symbology.

FIGURE 1. Physical dimensions (similar to TO-3).

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